

(12) 특허협력조약에 의하여 공개된 국제출원

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(43) 국제공개일
2011년 3월 24일 (24.03.2011)

PCT

(10) 국제공개번호
WO 2011/034273 A1

- (51) 국제특허분류:
H01L 33/42 (2010.01) H01L 33/14 (2010.01)
- (21) 국제출원번호: PCT/KR2010/003641
- (22) 국제출원일: 2010년 6월 7일 (07.06.2010)
- (25) 출원언어: 한국어
- (26) 공개언어: 한국어
- (30) 우선권정보:
10-2009-0088009 2009년 9월 17일 (17.09.2009) KR
- (71) 출원인 (US 을(를) 제외한 모든 지정국에 대하여): **주식회사 퀀텀디바이스 (QUANTUM DEVICE INC.)** [KR/KR]; 서울 강남구 청담동 88-37 인성빌딩 2층 202호, 135-954 Seoul (KR).
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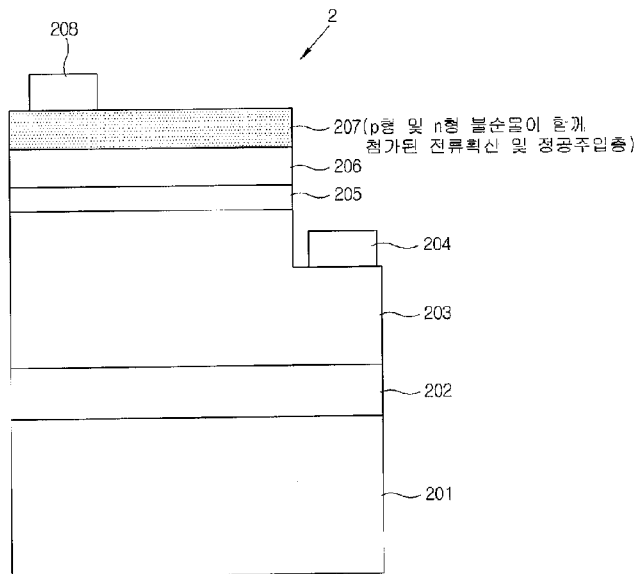
- (81) 지정국 (별도의 표시가 없는 한, 가능한 모든 종류의 국내 권리의 보호를 위하여): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PE, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.
- (84) 지정국 (별도의 표시가 없는 한, 가능한 모든 종류의 역내 권리의 보호를 위하여): ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), 유라시아 (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), 유럽 (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

[다음 쪽 계속]

(54) Title: SEMICONDUCTOR LIGHT-EMITTING DEVICE

(54) 발명의 명칭 : 반도체 발광소자

[Fig. 2]



207 ... current-spreading and hole injection layer in which both a p-type impurity and an n-type impurity are added together

(57) Abstract: The present invention relates to a semiconductor light-emitting device. The semiconductor light-emitting device comprises: a substrate; an n-type semiconductor layer for providing electrons when voltage is applied thereto; a p-type semiconductor layer for providing electron holes when voltage is applied thereto; a conductive n-type electrode for applying voltage to the n-type semiconductor layer; a conductive p-type electrode for applying voltage to the p-type semiconductor layer; an active layer which is interposed between the n-type semiconductor layer and the p-type semiconductor layer, and which has a quantum well structure for activating electron-hole combination; and a current-spreading and hole injection layer which is interposed between the p-type semiconductor layer and the p-type electrode, and in which both an n-type impurity and a p-type impurity are doped together for current-spreading and hole injection between the p-type electrode and the p-type semiconductor layer. Consequently, the semiconductor light-emitting device of the present invention is advantageous in that it not only reduces contact resistance between an electrode and a semiconductor layer, improving current flow and rendering current-spreading further uniform, but also improves hole injection performance, thereby achieving the maximized efficiency of the device.

(57) 요약서:

[다음 쪽 계속]